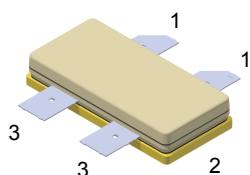


RF power transistors HF/VHF/UHF N-channel MOSFET



STAC780-4F

Pin connection	
Pin	Connection
1	Drain
2	Source (bottom side)
3	Gate

Features

Order code	Frequency	V _{DD}	P _{OUT}	Gain	Efficiency
STAC4932F	123 MHz	100 V	1000 W	26 dB	60 %

- Excellent thermal stability
- Common source push-pull configuration
- P_{OUT} = 1000 W min. (1200 W typ.) with 26 dB gain at 123 MHz
- Pulse conditions: 1ms, 10%
- In compliance with the 2002/95/EC European directive
- ST air-cavity STAC packaging technology

Description

The **STAC4932F** is a N-channel MOS field-effect RF power transistor. It is intended for 100 V pulse applications up to 250 MHz. This device is suitable for use in industrial, scientific and medical applications.

The **STAC4932F** benefits from the latest generation of efficient, patent-pending package technology, otherwise known as STAC.



Product status link
STAC4932F

Product summary	
Order code	STAC4932F
Marking	STAC4932F
Package	STAC780-4F
Packing	Box
Base / Bulk qty	20 / 80

1 Electrical data

1.1 Maximum ratings

Table 1. Absolute maximum ratings ($T_{CASE} = 25\text{ °C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain source voltage ($V_{GS} = 0\text{ V}$, $T_J = 150\text{ °C}$)	200	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 1\text{ M}\Omega$)	200	V
V_{GS}	Gate-source voltage	± 20	V
T_J	Maximum operating junction temperature	200	°C
T_{STG}	Storage temperature range	-65 to +150	°C

1.2 Thermal data

Table 2. Thermal data (1ms, 10%)

Symbol	Parameter	Value	Unit
R_{thJC}	Junction-case thermal resistance	0.075	°C/W

1.3 ESD protection characteristics

Table 3. ESD protection

Symbol	Test Methodology	Class
HBM	Human Body Model (per JESD22-A114)	2

2 Electrical characteristics

$T_{CASE} = +25\text{ }^{\circ}\text{C}$ (unless otherwise specified)

2.1 Static

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain - source Breakdown voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 100\text{ mA}$, $T_J = 150\text{ }^{\circ}\text{C}$	200	250		V
I_{DSS}	Zero gate voltage drain leakage current	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$			1	mA
I_{GSS}	Gate - source leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			250	nA
V_{TH}	Gate - source threshold voltage	$I_{DS} = 250\text{ mA}$	2		4	V
$V_{DS(ON)}$	Drain - source on voltage	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$			3.6	V
G_{FS}	Forward transconductance	$V_{DS} = 10\text{ V}$, $I_D = 2.5\text{ A}$		6		S
C_{ISS}	Input capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$		570		pF
C_{OSS}	Output capacitance			134		pF
C_{RSS}	Reverse transfer capacitance			8		pF

2.2 Dynamic

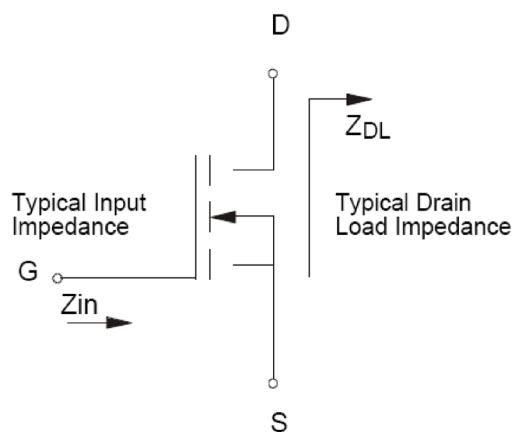
Table 5. Dynamic ⁽¹⁾

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
P_{OUT}	Output power		1000	1200	-	W
η_D	Drain efficiency	$P_{OUT} = 1000\text{ W}$		60	-	%
G_{ps}	Power gain	$P_{OUT} = 1000\text{ W}$		26	-	dB

1. $V_{DD} = 100\text{ V}$, $I_{DQ} = 2 \times 250\text{ mA}$, $f = 123\text{ MHz}$, $PW\ 1\text{ ms}$, $DC = 10\%$

3 Impedance

Figure 1. Current conventions



GADG170720191138MT

Table 6. Impedance data

Freq. (MHz)	$Z_{IN} (\Omega)$	$Z_{DL}(\Omega)$
123	TBD	$7.63 + j\ 2.92$

Note: Measured gate-to-gate and drain-to-drain, respectively (balanced configuration).

4 Typical performance

Figure 2. Safe operating area

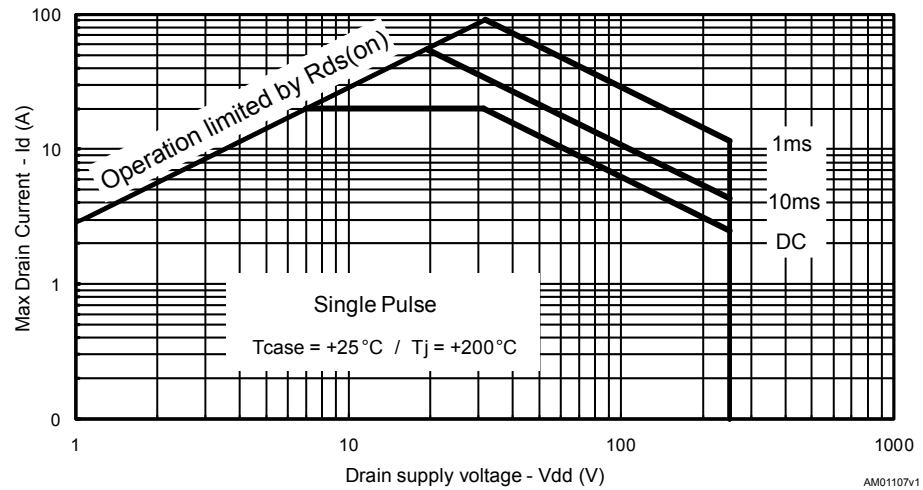


Figure 3. Transient thermal impedance

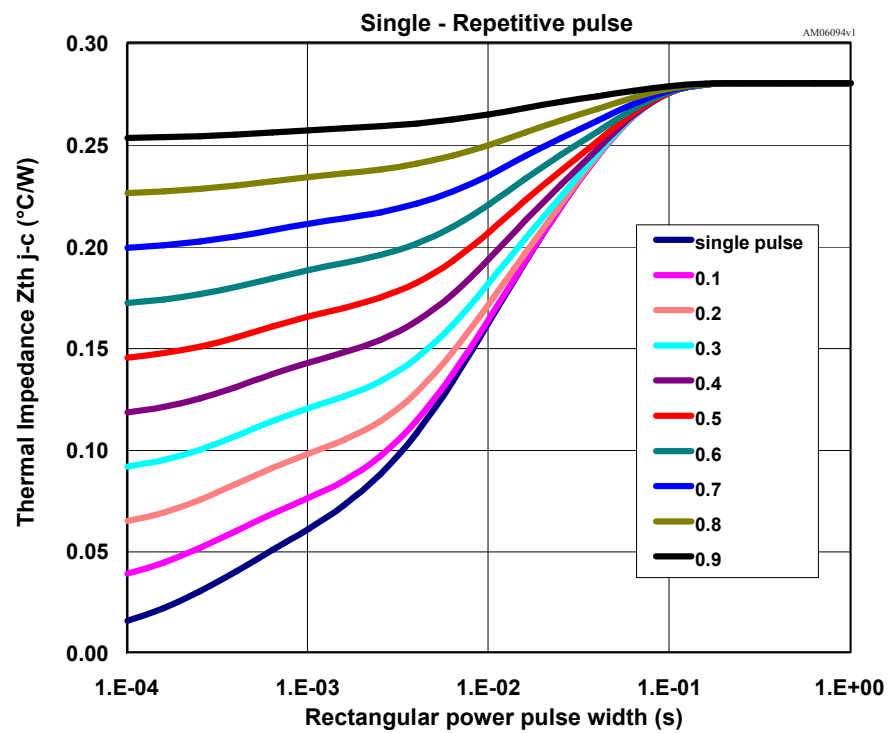
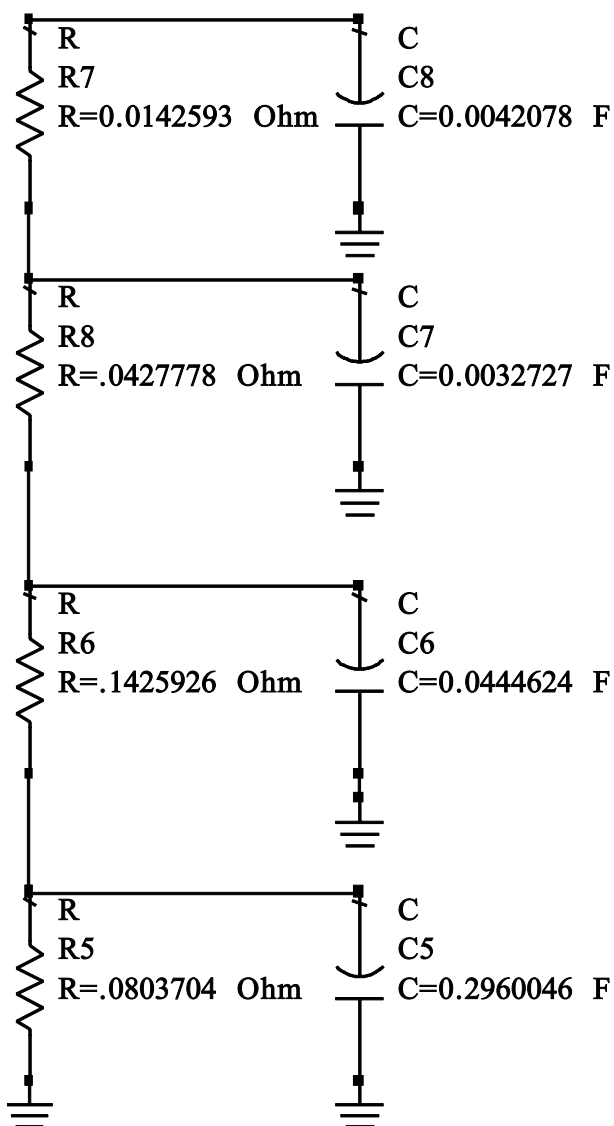


Figure 4. Transient thermal model



AM06106v1

Figure 5. Power gain versus output power

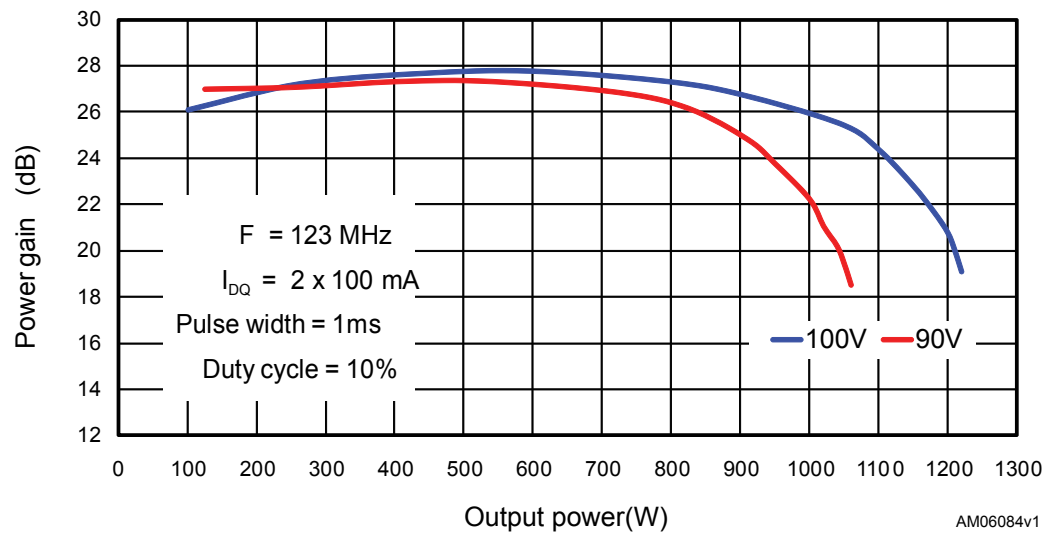
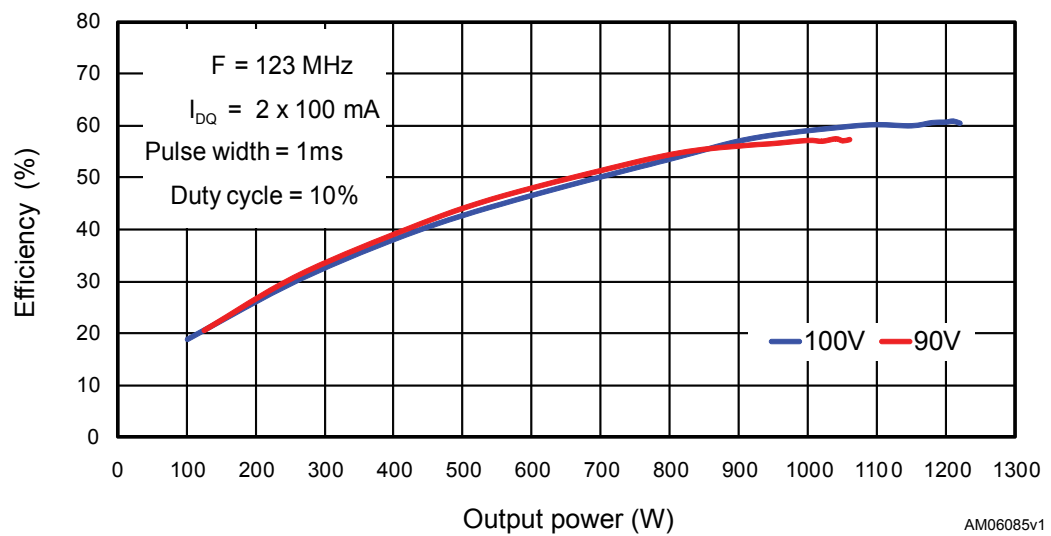


Figure 6. Efficiency versus output power

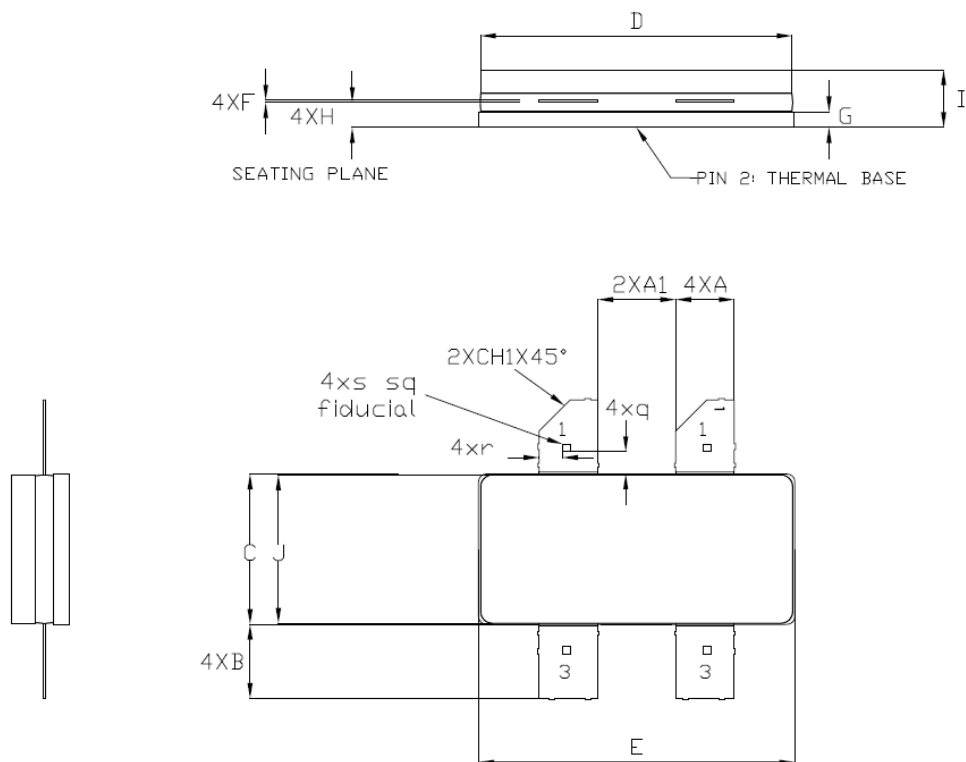


5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

5.1 STAC780-4F package information

Figure 7. STAC780-4F package outline



PIN	CONNECTIO N
1	DRAIN
2	SOURCE
3	GATE

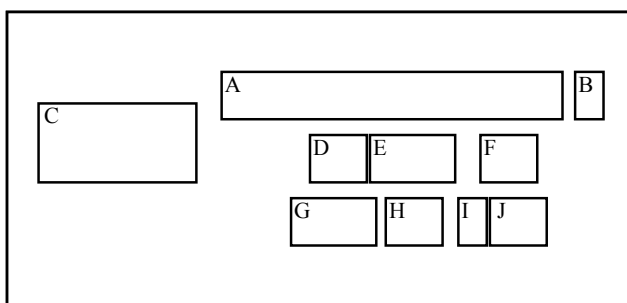
DM00481940-1

Table 7. STAC780-4F mechanical data

Ref.	Millimeters		
	Min.	Typ.	Max.
A	3.76		3.86
A1	5.03		5.13
B	4.57		5.08
C	9.65		9.91
D	20.17		20.37
E	20.45		20.70
F	0.11		0.17
G	0.97		1.14
H	1.52		1.70
I	3.18		4.32
J	9.52		9.78
q		1.37	
r		1.52	
s		0.51	
CH1		2.03	

5.2 Marking information

PACKAGE FACE TOP



LEGEND

-  Marking Composition Field
- A - MARKING AREA
- B - ADDITIONAL INFORMATION
(MAX CHAR ALLOWED = 1)
- C - STANDARD ST LOGO
- D - Assy Plant
(PP)
- E - FE Sequence
(nnn)
- F - Diffusion Traceability Plant
(WX)
- G - COUNTRY OF ORIGIN
(MAX CHAR ALLOWED = 3)
- H - Test and Finishing Plant
(TF)
- I - Assy Year
(Y)
- J - Assy Week
(WW)

Revision history

Table 8. Document revision history

Date	Version	Changes
22-Feb-2010	1	First release.
03-Aug-2010	2	Updated description on cover page and Table 3.
02-Sep-2010	3	Updated Figure 8. Added Figure 3, 4 and 5.
10-Apr-2020	4	Updated package information. Added Section 1.3 ESD protection characteristics .

Contents

1	Electrical data	2
1.1	Maximum ratings	2
1.2	Thermal data	2
1.3	ESD protection characteristics	2
2	Electrical characteristics	3
2.1	Static	3
2.2	Dynamic	3
3	Impedance	4
4	Typical performance	5
5	Package information	8
5.1	STAC780-4F package information	8
5.2	Marking information	10
	Revision history	11
	Contents	12

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